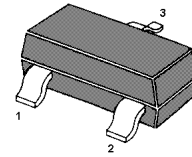
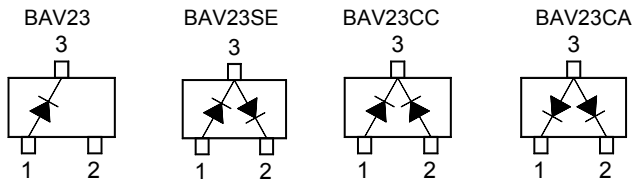


BAV23 / SE / CC / CA

Silicon Epitaxial Planar Diodes

High Voltage Switching Diode



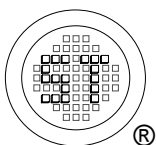
BAV23SE Marking Code: **PY**
 BAV23CC Marking Code: **PZ**
 BAV23CA Marking Code: **RA**
 SOT-23 Plastic Package

Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Maximum Repetitive Reverse Voltage	V_{RRM}	250	V
Reverse Voltage	V_R	200	V
Forward Current	I_F	400	mA
Repetitive Peak Forward Current	I_{FRM}	625	mA
Non-repetitive Peak Forward Surge Current	I_{FSM}	1.7 3 9	A
		at $t = 10\text{ ms}$ at $t = 100\ \mu\text{s}$ at $t = 1\ \mu\text{s}$	
Power Dissipation	P_D	350	mW
Thermal Resistance Junction to Ambient Air	$R_{\theta JA}$	357	$^\circ\text{C/W}$
Operating Junction and Storage Temperature Range	T_j, T_{stg}	- 65 to + 150	$^\circ\text{C}$

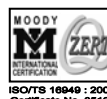
Electrical Characteristics ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Min.	Max.	Unit
Reverse Breakdown Voltage at $I_R = 100\ \mu\text{A}$	$V_{(BR)R}$	250	-	V
Forward Voltage at $I_F = 100\text{ mA}$ at $I_F = 200\text{ mA}$	V_F	- -	1 1.25	V
Reverse Current at $V_R = 200\text{ V}, T_j = 25^\circ\text{C}$ at $V_R = 200\text{ V}, T_j = 150^\circ\text{C}$	I_R	- -	100 100	nA μA
Total Capacitance at $V_R = 0\text{ V}, f = 1\text{ MHz}$	C_T	-	5	pF
Reverse Recovery Time at $I_F = I_R = 30\text{ mA}, I_{tr} = 0.1 \times I_R, R_L = 100\ \Omega$	t_{rr}	-	50	ns

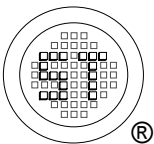
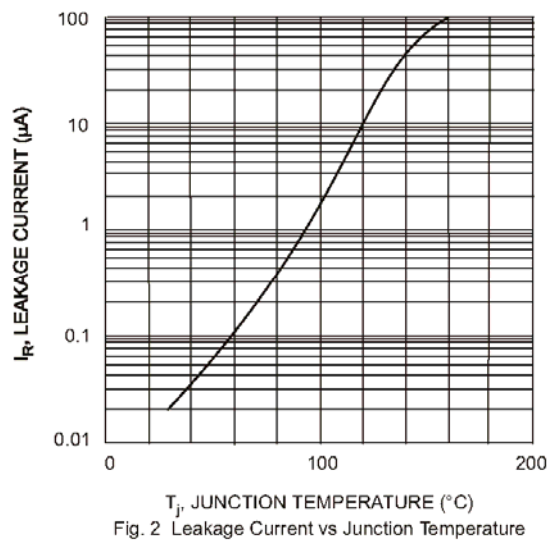
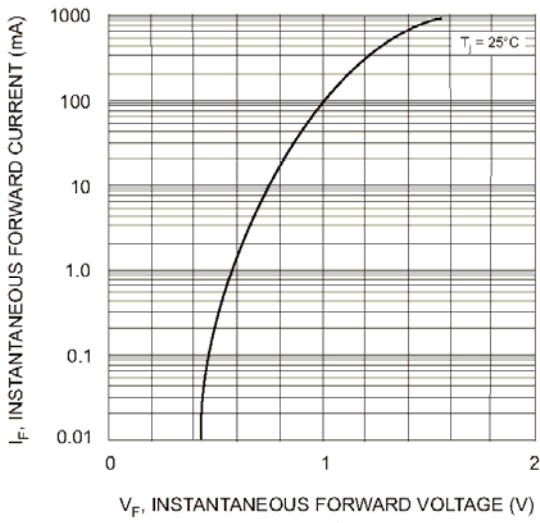


SEMTECH ELECTRONICS LTD.

(Subsidiary of Sino-Tech International Holdings Limited, a company listed on the Hong Kong Stock Exchange, Stock Code: 724)



Dated : 15/06/2009



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